



No.5064A

2SJ420

P-Channel Silicon MOSFET
Ultrahigh-Speed
Switching Applications

Features

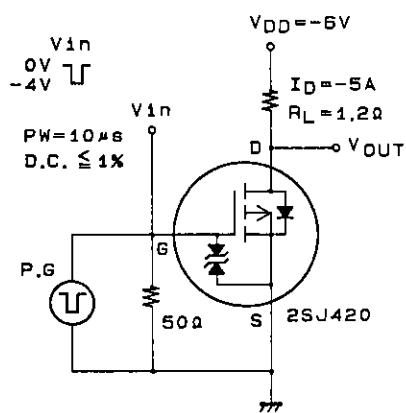
- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Absolute Maximum Ratings at Ta=25°C

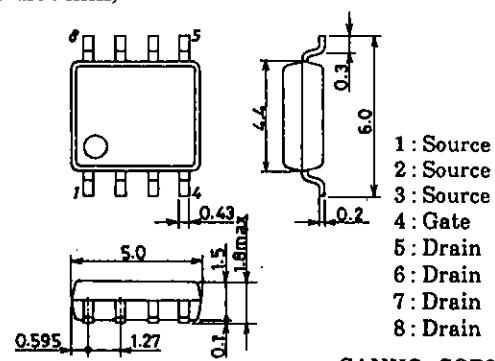
			unit
Drain-to-Source Voltage	V _{DSS}	-12	V
Gate-to-Source Voltage	V _{GSS}	±10	V
Drain Current (DC)	I _D	-5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1% -32	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1000mm ² ×0.8mm) 2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{tsg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} =0	-12			V
Zero-Gate Voltage	I _{DSS}	V _{DS} = -10V, V _{GS} =0			-100	μA
Drain Current						
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -6V, I _D = -1mA	-0.4		-1.4	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -6V, I _D = -5A	8	12		S
Static Drain-to-Source	R _{DS(on)1}	I _D = -5A, V _{GS} = -4V		50	63	mΩ
ON-State Resistance	R _{DS(on)2}	I _D = -2A, V _{GS} = -2.5V		70	108	mΩ
Input Capacitance	C _{iss}	V _{DS} = -6V, f=1MHz	1200			pF
Output Capacitance	C _{oss}	V _{DS} = -6V, f=1MHz	1100			pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -6V, f=1MHz	400			pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		25		ns
Rise Time	t _r	"		150		ns
Turn-OFF Delay Time	t _{d(off)}	"		150		ns
Fall Time	t _f	"		180		ns
Diode Forward Voltage	V _{SD}	I _S = -5A, V _{GS} =0	-1.0	-1.2		V

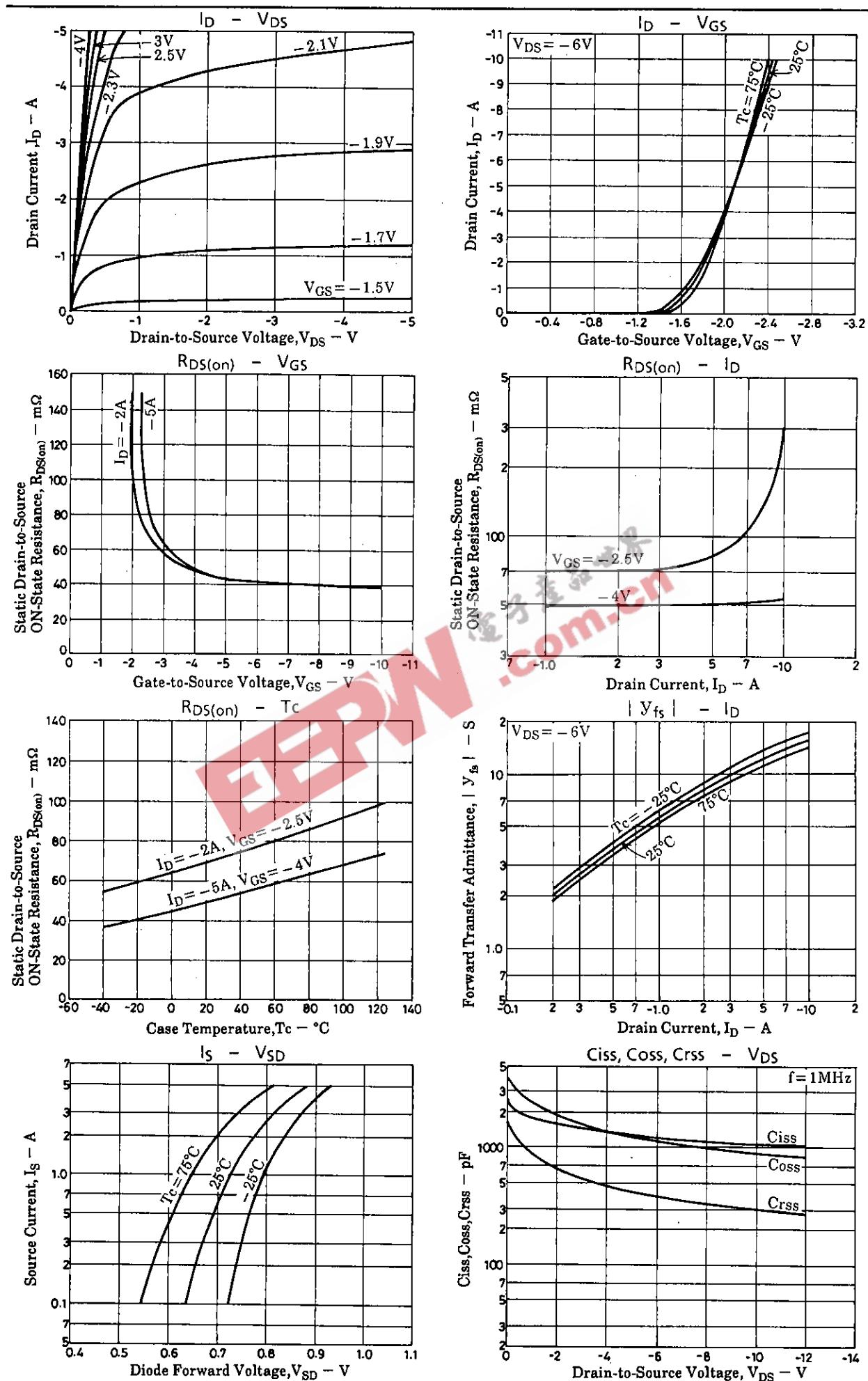
Switching Time Test Circuit

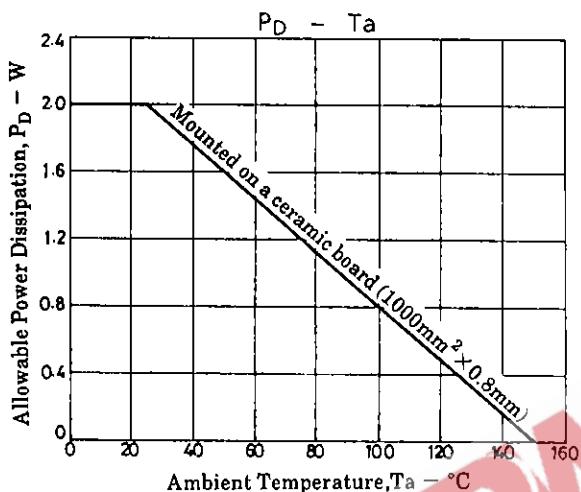
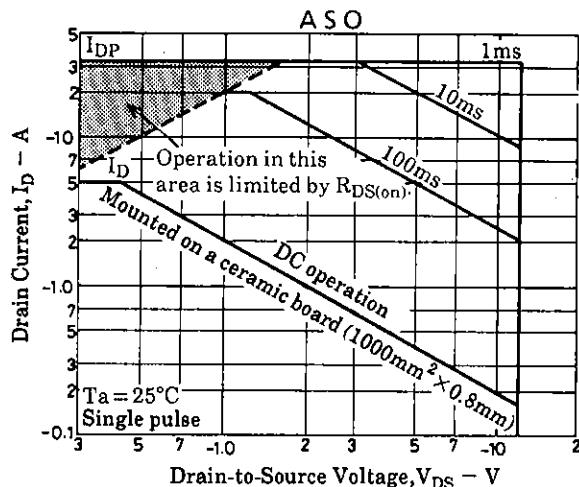
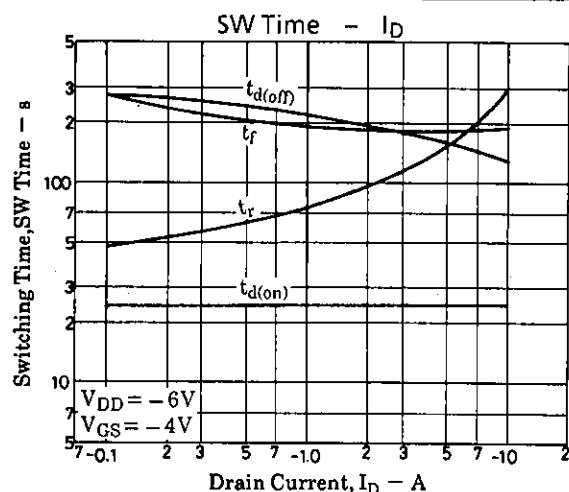
Package Dimensions 2116
(unit : mm)



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